GSSP600A Series

6.0A Silicon Rectifiers

Product Description

Reverse Voltage 50V To 1000V Forward Current 6.0A

Features

- Low Forward Voltage Drop
- High Current Capacity
- High Reliability
- High Surge Current Capability
- Lead(Pb)-Free

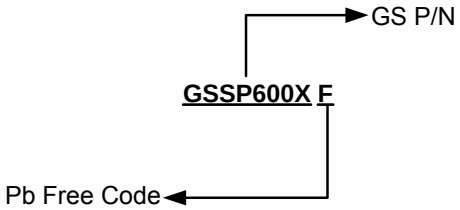
Mechanical Data

- Case : Molded Plastic
- Epoxy : UL 94V-0 rate flame retardant
- Lead : Axial leads, solderable per MIL-STD-202, method 208 guaranteed
- Polarity : Color band denotes cathode end
- Mounting position : Any
- Weight : 1.65 grams

Packages

R-6

Ordering Information



P/N	Package
GSSP600AF	R-6
GSSP600BF	R-6
GSSP600DF	R-6
GSSP600GF	R-6
GSSP600JF	R-6
GSSP600KF	R-6
GSSP600MF	R-6

Electrical Characteristics

Rating 25˚C Ambient Temperature Unless Otherwise Specified.
Single Phase Half Wave, 60Hz , Resistive or Inductive Load.
For Capacitive Load, Derate Current by 20%.

Symbol	Conditions		P600A	P600B	P600D	P600G	Unit
V_{RRM}	Maximum Recurrent Peak Reverse Voltage		50	100	200	400	V
V_{RMS}	Maximum RMS Voltage		35	70	140	280	V
V_{DC}	Maximum DC Blocking Voltage		50	100	200	400	V
Symbol	**Conditions**		**P600J**	**P600K**	**P600M**		**Unit**
V_{RRM}	Maximum Recurrent Peak Reverse Voltage		600	800	1000		V
V_{RMS}	Maximum RMS Voltage		420	560	700		V
V_{DC}	Maximum DC Blocking Voltage		600	800	1000		V
$I_{F(AV)}$	Maximum Average Forward Rectifier Current .375" (9.5m) Lead length at T_A=60˚C		6.0				A
I_{FSM}	Peak Forward Surge Current, 8.3 ms Single Half Sine-Wave Superimposed on Rated Load (JEDEC Method)		400				A
V_F	Maximum Instantaneous at 6.0A DC		0.95				V
C_J	Typical Junction Capacitance (Note 1)		100				pF
I_R	Maximum DC Reverse Current At Rated DC Blocking Voltage	T_J=25°C	10				uA
		T_J=100°C	400				
$R_{\Theta JA}$	Typical Thermal Resistance (Note 2)		10				°C/W
T_J	Junction Temperature Range		-65 to +175				°C
T_{STG}	Storage Temperature Range		-65 to +175				°C

Notes: 1. Measured at 1.0MHz applied reverse voltage of 4.0V D.C
2. Thermal Resistance from Junction to Ambient .375" (9.5mm) lead length

Typical Characteristics

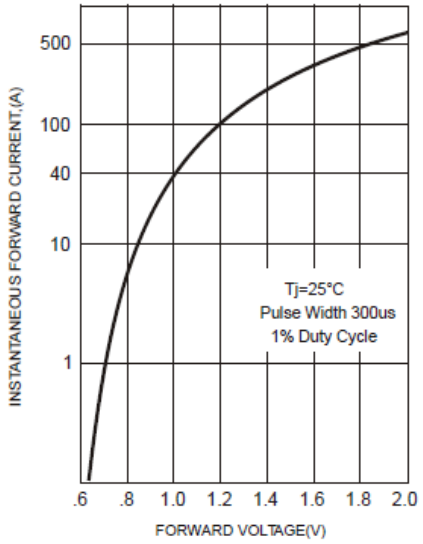


FIG.1-TYPICAL FORWARD CHARACTERISTICS

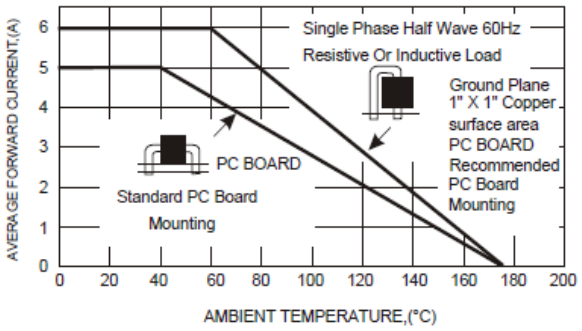


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

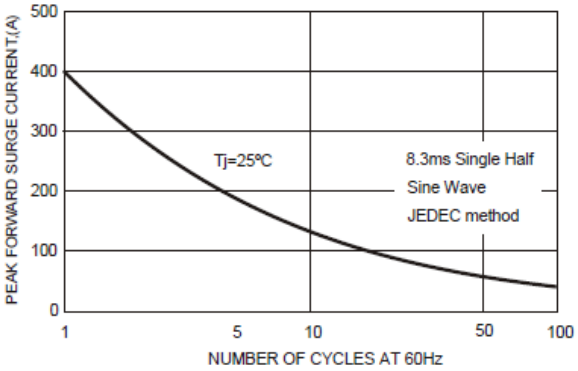


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

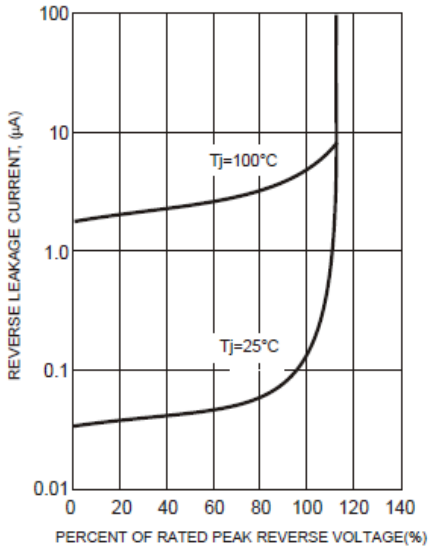


FIG.3 - TYPICAL REVERSE CHARACTERISTICS

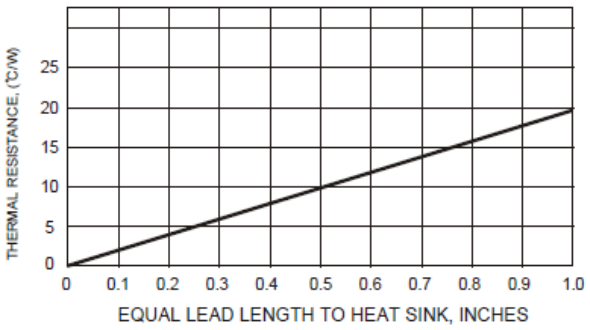
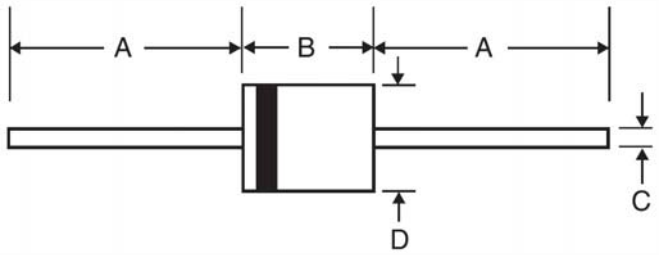


FIG.5 - TYPICAL THERMAL RESISTANCE VS. LEAD LENGTH

Package Dimension

R-6



Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	25.40	-	1.000	-
B	8.6	9.1	0.338	0.358
C	1.2	1.3	0.047	0.051
D	8.6	9.1	0.338	0.358

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